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**SEMIDRIVER™**

## Hybrid Dual IGBT Driver

### SKHI 24 (R)

Preliminary Data

### Features

- Dual driver for halfbridge IGBT modules
- For 1700 V - IGBT
- 5 V input level
- CMOS compatible inputs
- Short circuit protection by  $V_{CE}$  monitoring and switch off
- Drive interlock top/bottom
- Isolation by transformers
- Supply undervoltage protection (13 V)
- Error latch/output

### Typical Applications

- Driver for IGBT and MOSFET modules in bridge circuits, drives, UPS and welding inverters
- DC bus voltage up to 1200 V

1) At  $R_{CE} = 18 \text{ k}\Omega$ ,  $C_{CE} = 330 \text{ pF}$

2) At  $R_{CE} = 36 \text{ k}\Omega$ ,  $C_{CE} = 470 \text{ pF}$ ,  
 $R_{VCE} = 1 \text{ k}\Omega$

Absolute Maximum Ratings		$T_a = 25^\circ\text{C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
$V_S$	Supply voltage prim.	18	V
$V_{iH}$	Input signal volt. (High)	5 + 0,3	V
$I_{outPEAK}$	Output peak current	15	A
$I_{outAVmax}$	Output average current (max.)	80	mA
$f_{max}$	max. switching frequency	50	kHz
$V_{CE}$	Collector emitter voltage sense across the IGBT	1700	V
$dv/dt$	Rate of rise and fall of voltage secondary to primary side	50	kV/ $\mu\text{s}$
$V_{isolIO}$	Isolation test voltage input-output (2 sec. AC)	4000	V
$V_{isol12}$	Isolation test voltage output 1 - output 2 (2 sec. AC)	1500	V
$R_{Gonmin}$	Minimum rating for $R_{Gon}$	1,5	$\Omega$
$R_{Goffmin}$	Minimum rating for $R_{Goff}$	1,5	$\Omega$
$Q_{out/pulse}$	Max. rating for output charge per pulse	5	$\mu\text{C}$
$T_{op}$	Operating temperature	- 25 ... + 85	$^\circ\text{C}$
$T_{stg}$	Storage temperature	- 40 ... + 85	$^\circ\text{C}$

Characteristics		$T_a = 25^\circ\text{C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
$V_S$	Supply voltage primary side	14,4	15	15,6	V
$I_{SO}$	Supply current primary side (no load)		100		mA
	Supply current primary side (operation)			550	mA
$V_i$	Input signal voltage on / off		5 / 0		V
$V_{iT+}$	Input threshold voltage (High)	3,4	3,8	4,1	V
$V_{iT-}$	Input threshold voltage (Low)	1,5	1,9	2,2	V
$R_{in}$	Input resistance		3,3		k $\Omega$
$V_{G(on)}$	Turn-on gate voltage output		+15		V
$V_{G(off)}$	Turn-off gate voltage output		-8		V
$R_{GE}$	Internal gate-emitter resistance		22		k $\Omega$
$f_{ASIC}$	Asic system switching frequency		8		MHz
$t_{d(on)IO}$	Input-output turn-on propagation time	0,85	1	1,25	$\mu\text{s}$
$t_{d(off)IO}$	Input-output turn-off propagation time	0,85	1	1,25	$\mu\text{s}$
$t_{d(terr)}$	Error input-output propagation time		0,6		$\mu\text{s}$
$t_{pERRRESET}$	Error reset time		12		$\mu\text{s}$
$t_{TD}$	Top-Bot Interlock Dead Time	fig.2			$\mu\text{s}$
$V_{CEstat}$	Reference voltage for $V_{CE}$ -monitoring		5 <sup>1)</sup> / 6 <sup>2)</sup>	10	V
$C_{ps}$	Coupling capacitance primary secondary		18		pF
MTBF	Mean Time Between Failure $T_a = 40^\circ\text{C}$		1,6		10 <sup>6</sup> h
m	weight		115		g
HxBxT	Dimensions		20x57x114		mm

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